Unitized Semiconductor Devices - Page 1 of 1



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Inclos	ure Material:
Metal	
	II I on with a
	II Length: en 0.170 inches and 0.210 inches
	nal Length:
0.500 i	
	II Diameter: en 0.209 inches and 0.230 inches
	Electronic Device Engineering Council/jedec/case Outline Designation:
To-71	
-	onent Name And Quantity:
2 trans	
	ting Method:
Termir	
	nal Circle Diameter:
	res Provided:
	n and gold plated leads and hermetically sealed case
	onductor Material:
	all transistor
-	e Rating In Volts Per Characteristic:
	drain to gate voltage all transistor and 25.0 drain to source voltage all transistor
Curre	nt Rating Per Characteristic:
1.00 m	illiamperes gate current all transistor
Power	Rating Per Characteristic:
300.0	milliwatts total device dissipation all transistor
Maxim	num Operating Tempurature Per Measurement Point:
200.0	degrees celsius junction
Precio	ous Material And Location:
Termir	nal surfaces gold
Precio	ous Material:
Gold	
Termi	nal Type And Quantity:
6 unins	sulated wire lead
Shelf I	Life:
N/a	
Unit O	of Measure:
Demili	itarization:
No	
Fiig:	
A110a	0